

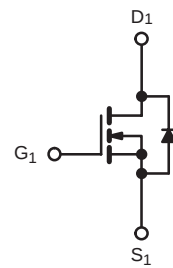
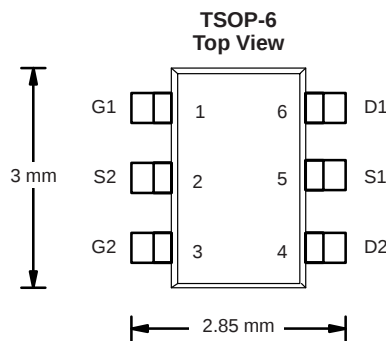
Dual N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY

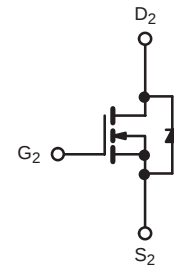
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
20	0.022 at $V_{GS} = 4.5$ V	6.0	1.8 nC
	0.028 at $V_{GS} = 2.5$ V	5.0	

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC


RoHS
 COMPLIANT


N-Channel MOSFET



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	$T_C = 25^\circ\text{C}$	6.0	A
	$T_C = 70^\circ\text{C}$	4.0	
	$T_A = 25^\circ\text{C}$	3.5 ^{b, c}	
	$T_A = 70^\circ\text{C}$	2.8 ^{b, c}	
Pulsed Drain Current	I_{DM}	18	A
Continuous Source-Drain Diode Current	$T_C = 25^\circ\text{C}$	1.17	
	$T_A = 25^\circ\text{C}$	0.95 ^{b, c}	
Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	1.6	W
	$T_C = 70^\circ\text{C}$	1.0	
	$T_A = 25^\circ\text{C}$	1.14 ^{b, c}	
	$T_A = 70^\circ\text{C}$	0.73 ^{b, c}	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	R_{thJA}	93	110	$^\circ\text{C/W}$
Maximum Junction-to-Foot	R_{thJF}	75	90	

Notes:

- $T_C = 25^\circ\text{C}$.
- Surface Mounted on 1" x 1" FR4 board.
- $t = 5$ s.
- Maximum under steady state conditions is 150°C/W .

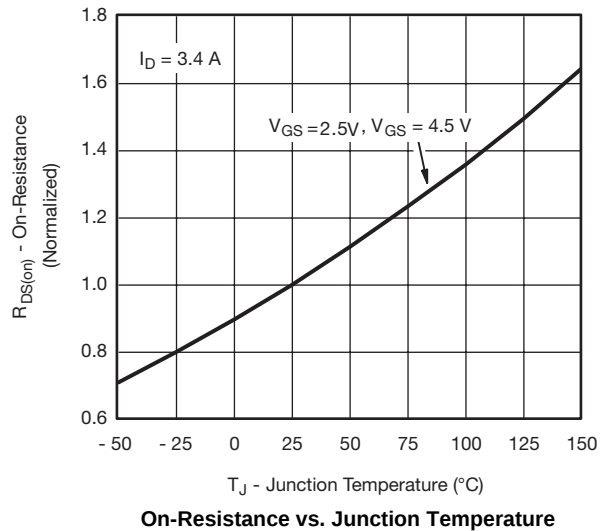
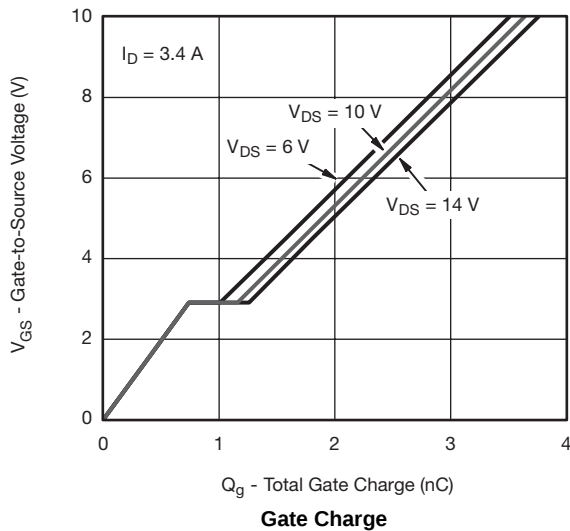
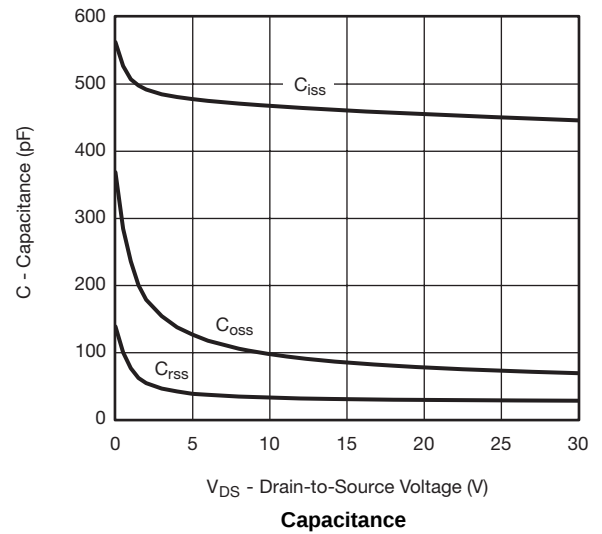
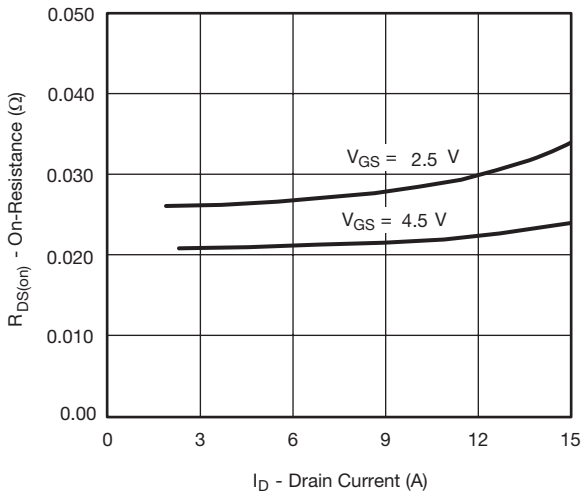
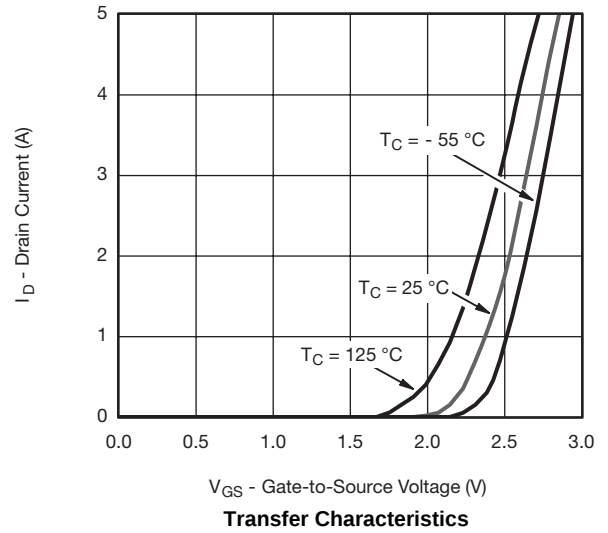
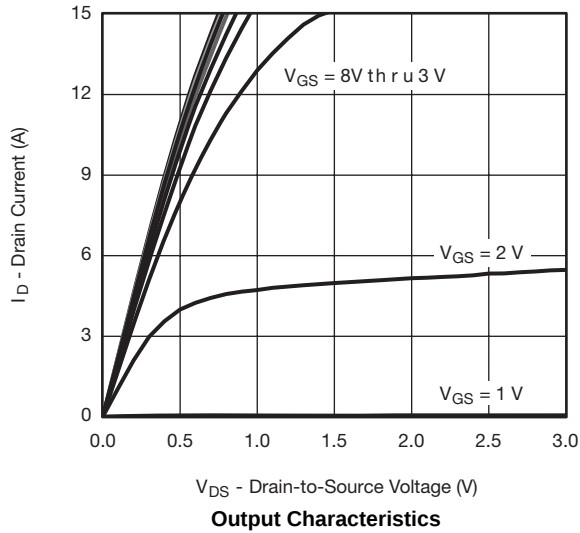
SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	20			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		29		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 4		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.4		1.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V			1	μA
		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	10			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 3.4 A		0.022		Ω
		V _{GS} = 2.5 V, I _D = 3.0 A		0.028		
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 3.4 A		10		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		400		pF
Output Capacitance	C _{oss}			55		
Reverse Transfer Capacitance	C _{rss}			26		
Total Gate Charge	Q _g	V _{DS} = 10 V, V _{GS} = 10 V, I _D = 3.4 A		3.7	6	nC
		V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 3.4 A		1.8	3	
Gate-Source Charge	Q _{gs}			0.74		
Gate-Drain Charge	Q _{gd}			0.42		
Gate Resistance	R _g	f = 1 MHz	1	5	10	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 10 V, R _L = 5.6 Ω I _D ≅ 2.7 A, V _{GEN} = 4.5 V, R _g = 1 Ω		10	20	ns
Rise Time	t _r			15	30	
Turn-Off Delay Time	t _{d(off)}			10	20	
Fall Time	t _f			10	20	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 10 V, R _L = 5.6 Ω I _D ≅ 2.7 A, V _{GEN} = 10 V, R _g = 1 Ω		5	10	
Rise Time	t _r			15	30	
Turn-Off Delay Time	t _{d(off)}			10	20	
Fall Time	t _f			10	20	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C		1.2		A
Pulse Diode Forward Current	I _{SM}			18		
Body Diode Voltage	V _{SD}	I _S = 2.7 A, V _{GS} = 0 V		0.85	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 2.7 A, dI/dt = 100 A/μs, T _J = 25 °C		10	20	ns
Body Diode Reverse Recovery Charge	Q _{rr}			4	10	nC
Reverse Recovery Fall Time	t _a			6		ns
Reverse Recovery Rise Time	t _b			4		

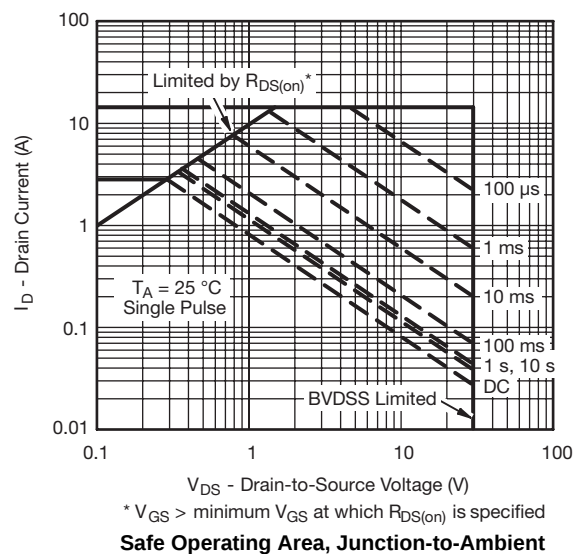
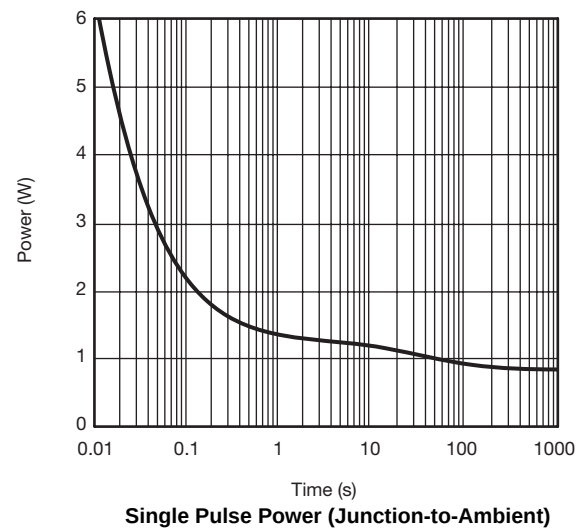
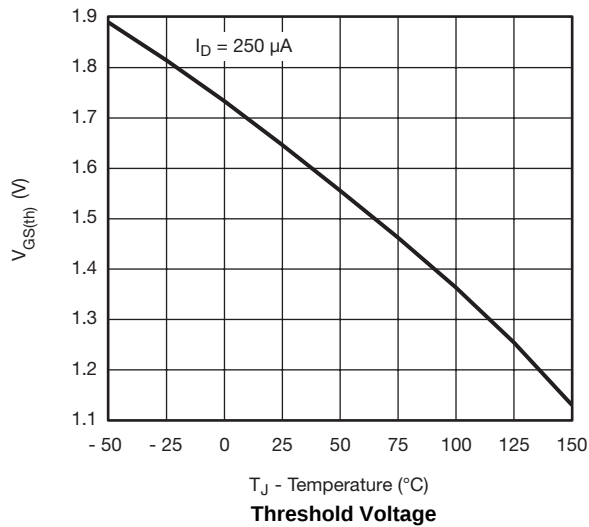
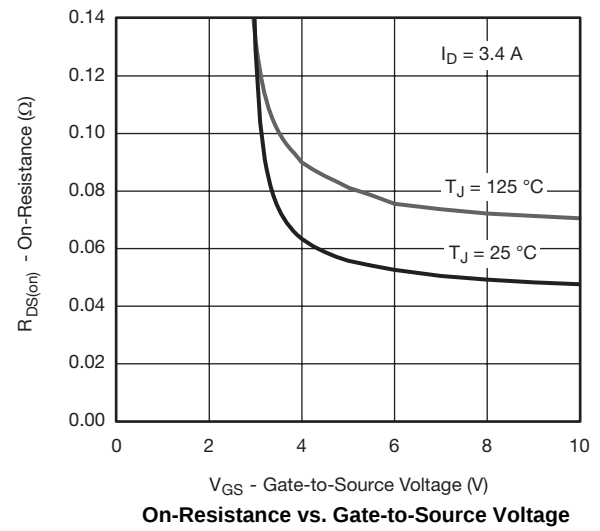
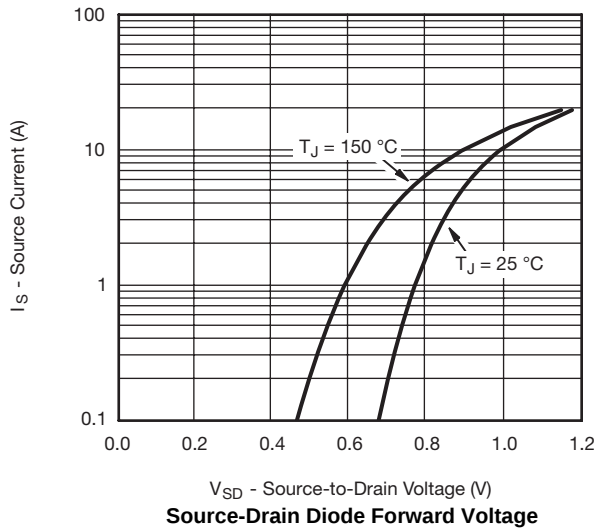
Notes:

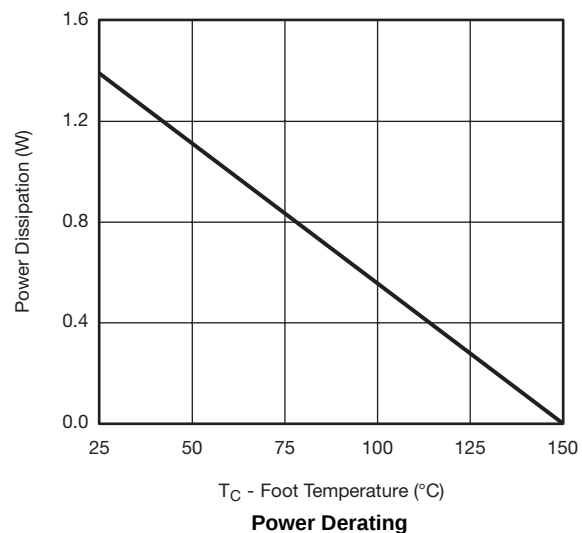
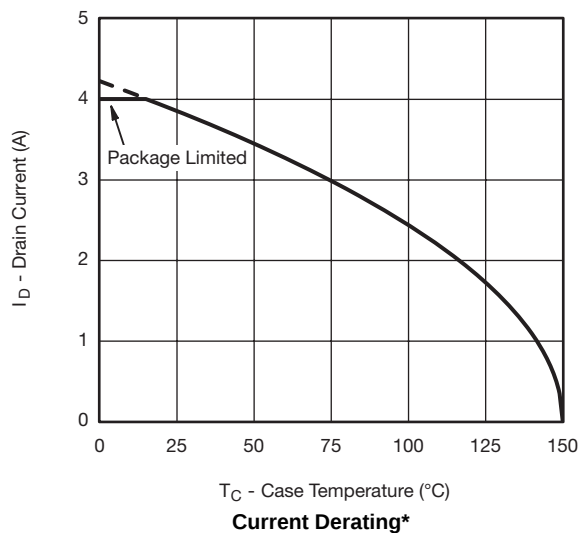
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

b. Guaranteed by design, not subject to production testing.

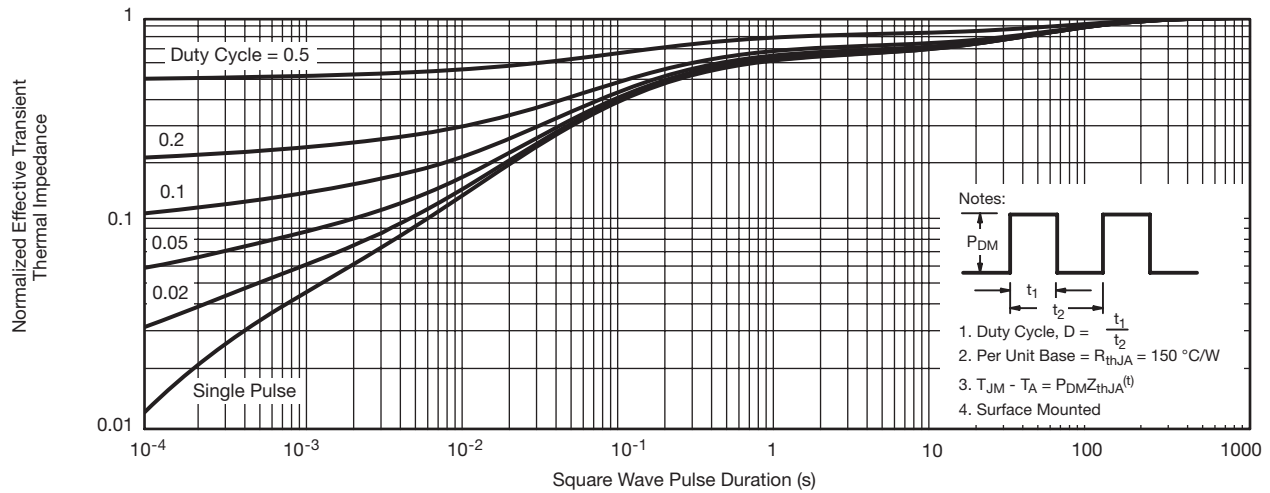
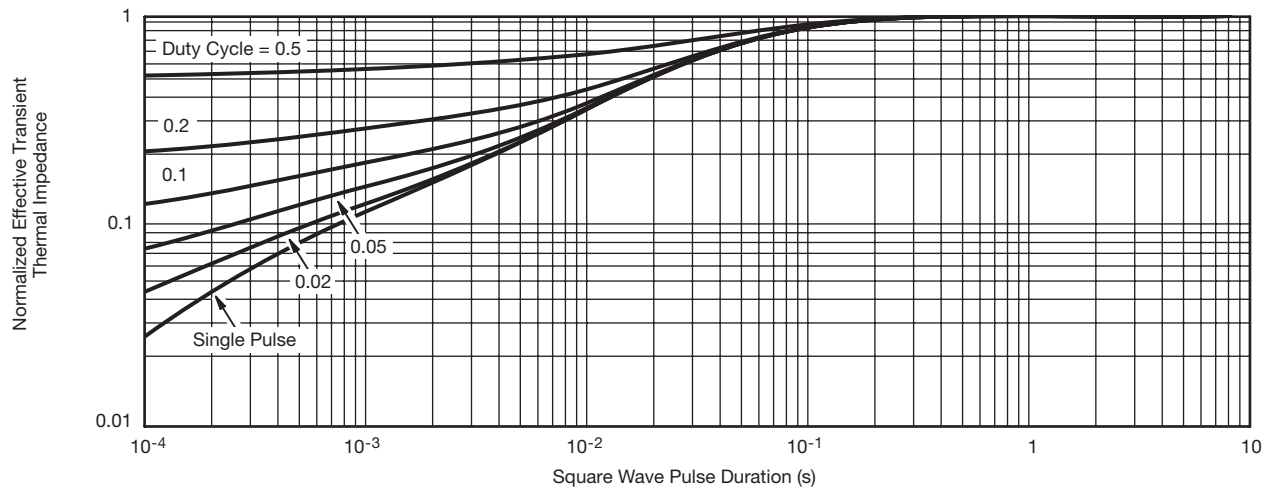
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


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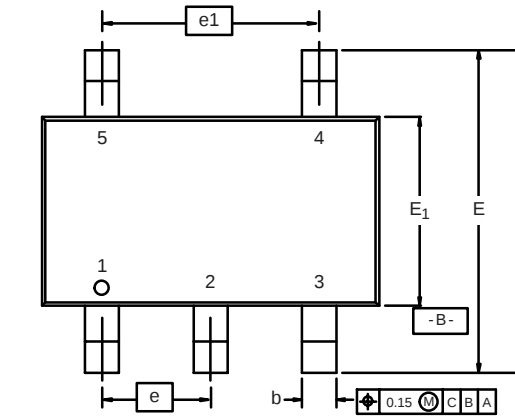
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

* The power dissipation P_D is based on $T_{J(max)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

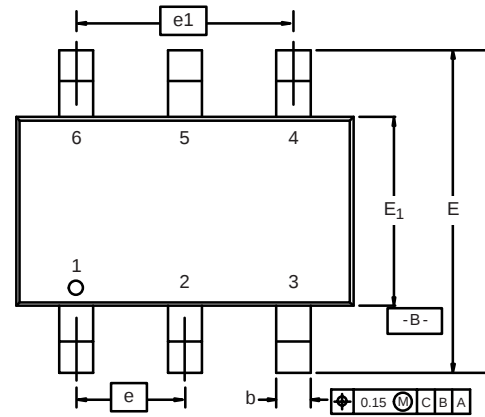
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Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Foot

TSOP: 5/6-LEAD

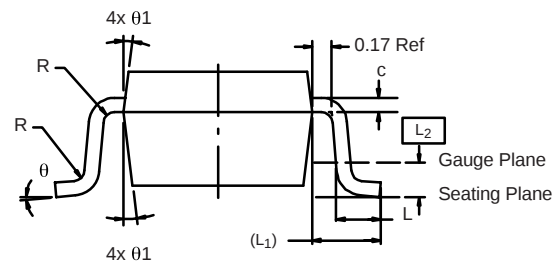
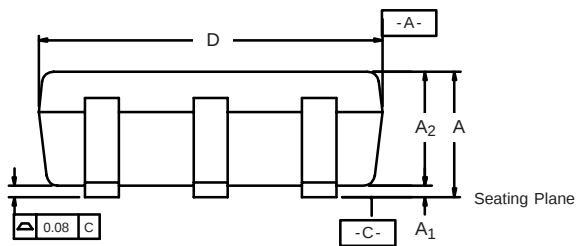
JEDEC Part Number: MO-193C



5-LEAD TSOP

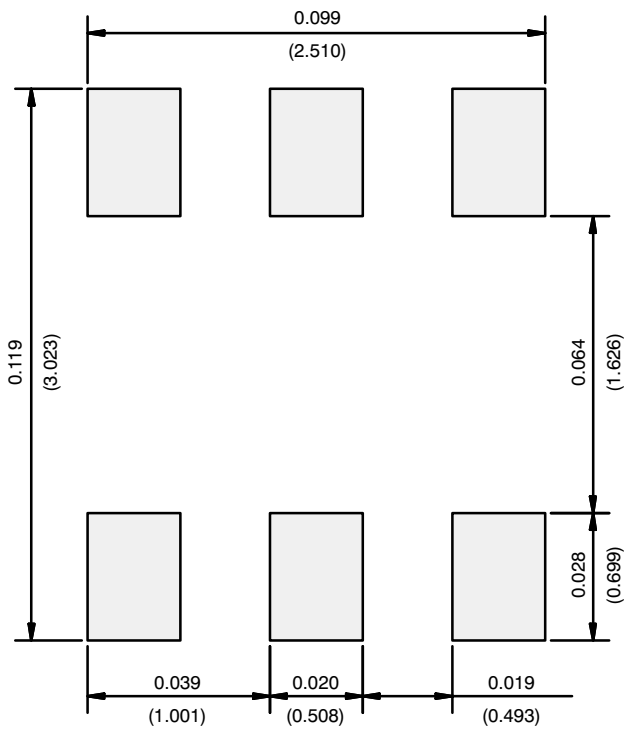


6-LEAD TSOP



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A ₁	0.01	-	0.10	0.0004	-	0.004
A ₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e ₁	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L ₁	0.60 Ref			0.024 Ref		
L ₂	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ ₁	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06						
DWG: 5540						

RECOMMENDED MINIMUM PADS FOR TSOP-6



Recommended Minimum Pads
Dimensions in Inches/(mm)

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